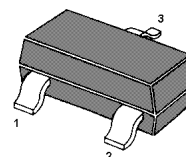


PNP General Purpose Transistor

for amplifier applications

On special request, these transistors can be manufactured in different pin configurations.



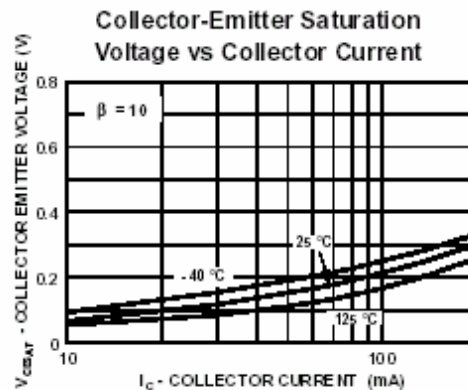
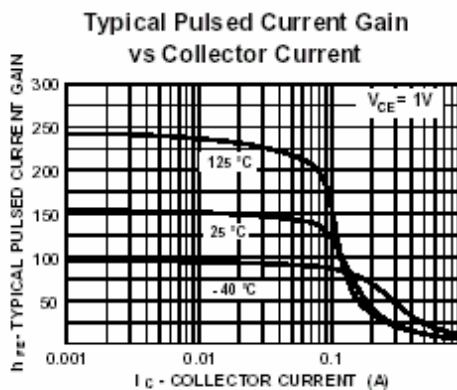
1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

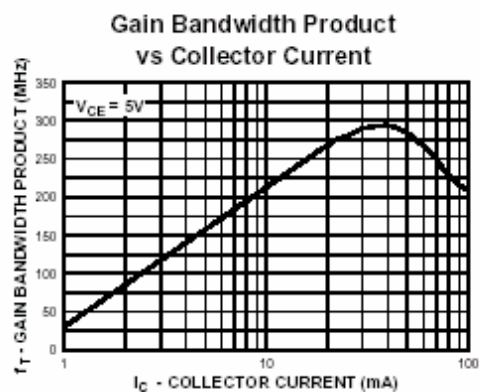
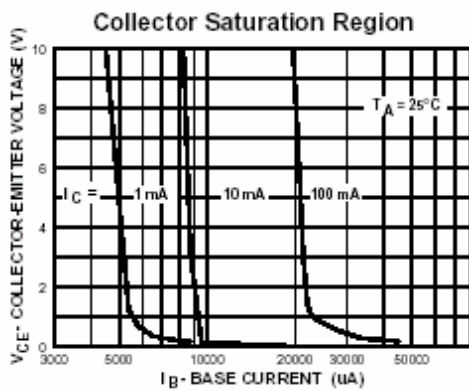
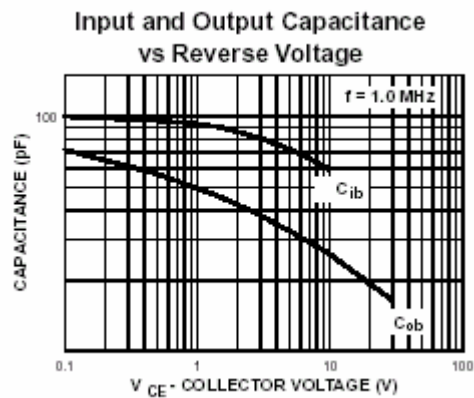
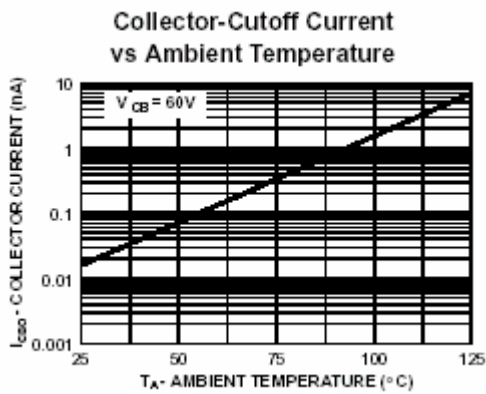
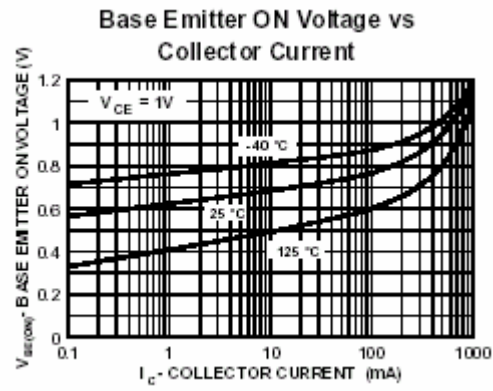
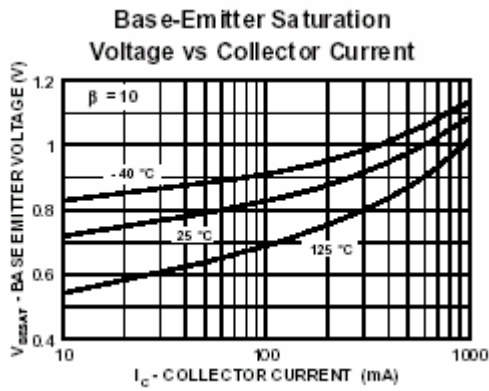
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	80	V
Collector Emitter Voltage	$-V_{CEO}$	80	V
Emitter Base Voltage	$-V_{EBO}$	4	V
Collector Current	$-I_C$	500	mA
Total Device Dissipation Derate above 25°C	P_{tot}	200 2.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_j	-55 to +150	°C
Storage Temperature Range	T_s	-55 to +150	°C

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-I_C=10\text{mA}$, $-V_{CE}=1\text{V}$	h_{FE}	100	-	-
at $-I_C=100\text{mA}$, $-V_{CE}=1\text{V}$	h_{FE}	100	-	-
Collector Cutoff Current				
at $-V_{CB}=80\text{V}$	$-I_{CBO}$	-	0.1	μA
Collector Cutoff Current				
at $-V_{CE}=60\text{V}$	$-I_{CEO}$	-	0.1	μA
Collector Emitter Breakdown Voltage				
at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	80	-	V
Collector Base Breakdown Voltage				
at $-I_C=100\mu\text{A}$	$-V_{(BR)CBO}$	80	-	V
Emitter Base Breakdown Voltage				
at $-I_E=100\mu\text{A}$	$-V_{(BR)EBO}$	4	-	V
Collector Emitter Saturation Voltage				
at $-I_C=100\text{mA}$, $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	0.25	V
Base Emitter On Voltage				
at $-I_C=100\text{mA}$, $-V_{CE}=1\text{V}$	$-V_{BE(on)}$	-	1.2	V
Current Gain – Bandwidth Product				
at $-I_C=100\text{mA}$, $-V_{CE}=1\text{V}$, $f=100\text{MHz}$	f_T	50	-	MHz



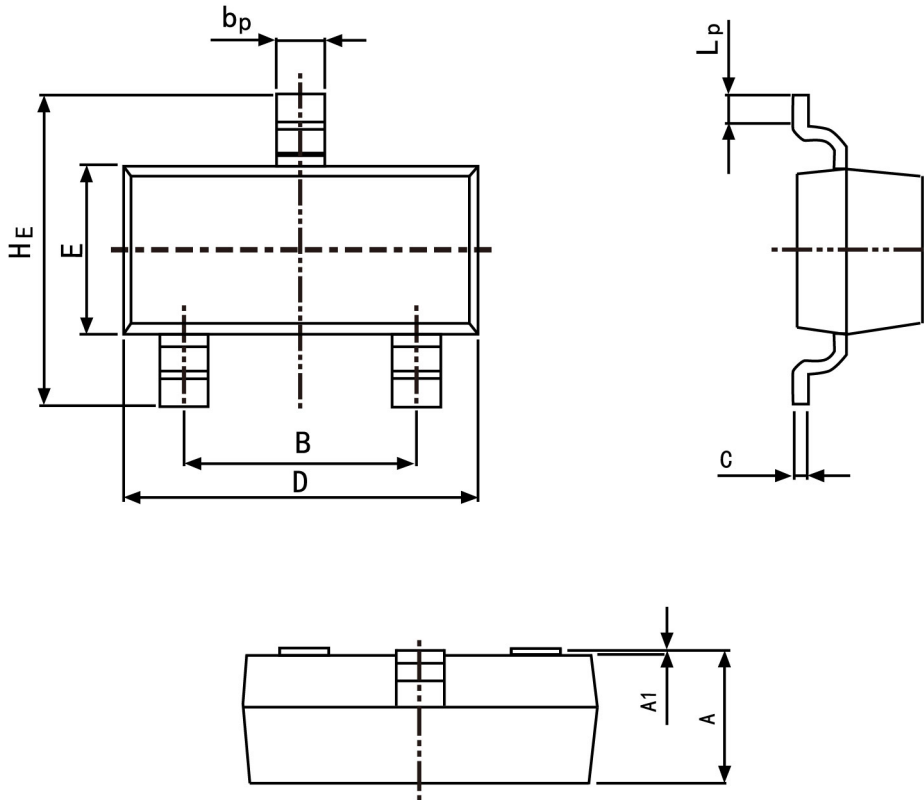




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
bp	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
A1	0.100	0.013
Lp	0.20	0.50